



# 2017 IEEE Pulsed Power Conference

## Tuesday, 20 June 2017

### Oral session 12 - Semiconductor components, Pulse Forming Networks and Alternate Technologies (part II) - Session

Chair : Luis Redondo - Preston (15:00 - 17:30)

time	[id] title	presenter
15:00	[74] Solid State Spark Gap and Ignitron Replacements	WALDRON, John
15:30	[214] HIGH-VOLTAGE PICOSECOND-RANGE AVALANCHE SWITCHING OF SEMICONDUCTOR STRUCTURES WITHOUT PN-JUNCTIONS	RODIN, Pavel
15:45	[355] The Progression of Silicon Carbide Power Devices Under The Army's High Voltage Power Technology Program	Dr HINOJOSA, Miguel
16:00	[227] Study on the high-power semi-insulating GaAs PCSS with quantum well structure	Dr LUAN, Chongbiao
16:15	[326] Narrow Pulse Evaluation of 15 kV SiC MOSFETs and IGBTs	BAYNE, Stephen
16:30	[203] INVESTIGATION OF FAST THYRISTOR SWITCHING MODULES TRIGGERED BY DIRECT OVERHEAD IGNITION	BISCHOFF, Rainer
17:00	[25] Silvaco-based evaluation of 10 kV 4H-SiC MOSFET as a solid-state switch in narrow-pulse application	Dr PUSHPAKARAN, Bejoy